

TrenchMV™ Power MOSFETs Common-Gate Pair

(Electrically Isolated Back Surface)

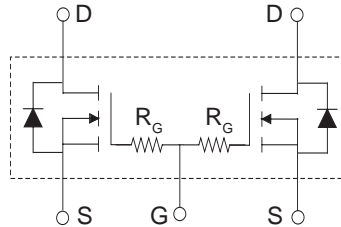
N-Channel Enhancement Mode
Avalanche Rated

IXTL2x240N055T

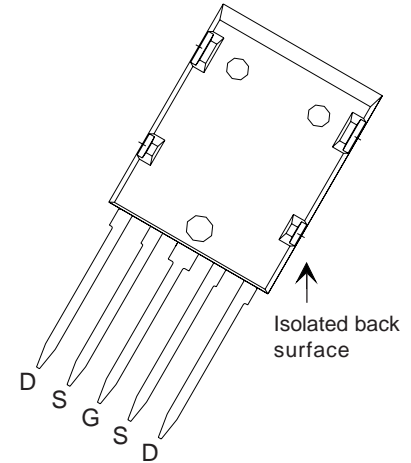
$$V_{DSS} = 55 \text{ V}$$

$$I_{D25} = 2 \times 140 \text{ A}$$

$$R_{DS(on)} \leq 4.4 \text{ m}\Omega$$



ISOPLUS i5-Pak™ (IXTL)



G = Gate
S = Source
D = Drain

Symbol	Test Conditions	Maximum Ratings	
V_{DSS}	$T_J = 25^\circ\text{C}$ to 175°C	55	V
V_{DGR}	$T_J = 25^\circ\text{C}$ to 175°C ; $R_{GS} = 1 \text{ M}\Omega$	55	V
V_{GSM}	Transient	± 20	V
I_{D25}	$T_C = 25^\circ\text{C}$ (Combined die total = 280 A)	140	A
I_{LRMS}	Package Current Limit, RMS (Combined die total = 150 A)	75	A
I_{DM}	$T_C = 25^\circ\text{C}$, pulse width limited by T_{JM}	650	A
I_{AS}	$T_C = 25^\circ\text{C}$	25	A
E_{AS}	$T_C = 25^\circ\text{C}$	1.0	J
dv/dt	$I_S \leq I_{DM}$, $di/dt \leq 100 \text{ A}/\mu\text{s}$, $V_{DD} \leq V_{DSS}$ $T_J \leq 175^\circ\text{C}$, $R_G = 3.3 \Omega$	3	V/ns
P_D	$T_C = 25^\circ\text{C}$	150	W
T_J		-55 ... +175	$^\circ\text{C}$
T_{JM}		175	$^\circ\text{C}$
T_{stg}		-55 ... +175	$^\circ\text{C}$
T_L	1.6 mm (0.062 in.) from case for 10 s Plastic body for 10 seconds	300 260	$^\circ\text{C}$ $^\circ\text{C}$
V_{ISOL}	50/60 Hz, $t = 1$ minute, $I_{ISOL} < 1 \text{ mA}$, RMS	2500	V
F_C	Mounting force	30..170 / 7..36	N/lb.
Weight	Package	9	g

Features

- Ultra-low On Resistance
- Unclamped Inductive Switching (UIS) rated
- Low package inductance
- easy to drive and to protect
- 175°C Operating Temperature

Advantages

- Easy to mount
- Space savings
- High power density

Applications

- Automotive
 - Motor Drives
 - High Side Switch
 - 12V Battery
 - ABS Systems
- DC/DC Converters and Off-line UPS
- Primary- Side Switch
- High Current Switching Applications

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$ unless otherwise specified)	Characteristic Values		
		Min.	Typ.	Max.
BV_{DSS}	$V_{GS} = 0 \text{ V}$, $I_D = 250 \mu\text{A}$	55		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 250 \mu\text{A}$	2.0		4.0 V
I_{GSS}	$V_{GS} = \pm 20 \text{ V}$, $V_{DS} = 0 \text{ V}$			$\pm 200 \text{ nA}$
I_{DSS}	$V_{DS} = V_{DSS}$ $V_{GS} = 0 \text{ V}$ $T_J = 150^\circ\text{C}$			5 μA 250 μA
$R_{DS(on)}$	$V_{GS} = 10 \text{ V}$, $I_D = 50 \text{ A}$, Note 1, 2			4.4 m Ω

All ratings and parametric values are per each MOSFET die unless otherwise specified.

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Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$ unless otherwise specified)		
		Min.	Typ.	Max.
g_{fs}	$V_{DS} = 10\text{ V}; I_D = 60\text{ A}$, Note 1	80	132	S
R_G			3	Ω
C_{iss}	$V_{GS} = 0\text{ V}, V_{DS} = 25\text{ V}, f = 1\text{ MHz}$		7600	pF
C_{oss}		1240	pF	
C_{rss}		260	pF	
$t_{d(on)}$	$V_{GS} = 10\text{ V}, V_{DS} = 0.5 V_{DSS}, I_D = 25\text{ A}$ $R_G = 5\ \Omega$ (External)		40	ns
t_r		54	ns	
$t_{d(off)}$		63	ns	
t_f		75	ns	
$Q_{g(on)}$	$V_{GS} = 10\text{ V}, V_{DS} = 0.5 V_{DSS}, I_D = 25\text{ A}$		170	nC
Q_{gs}		32	nC	
Q_{gd}		48	nC	
R_{thJC}			1.0	$^\circ\text{C/W}$
R_{thCS}		0.25		$^\circ\text{C/W}$

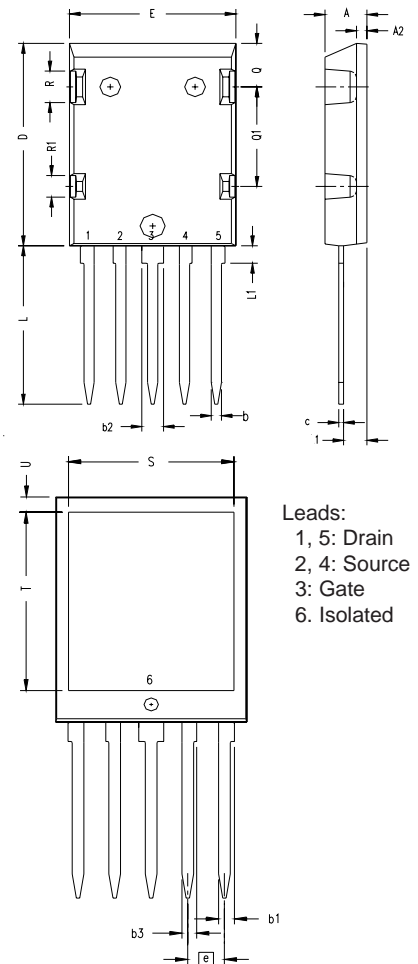
Source-Drain Diode		Characteristic Values ($T_J = 25^\circ\text{C}$ unless otherwise specified)		
Symbol	Test Conditions	Min.	Typ.	Max.
I_S	$V_{GS} = 0\text{ V}$			240 A
I_{SM}	Pulse width limited by T_{JM}			650 A
V_{SD}	$I_F = 50\text{ A}, V_{GS} = 0\text{ V}$, Note 1			1.0 V
t_{rr}	$I_F = 25\text{ A}, -di/dt = 100\text{ A}/\mu\text{s}$ $V_R = 30\text{ V}, V_{GS} = 0\text{ V}$		40	ns

- Notes: 1. Pulse test, $t \leq 300\ \mu\text{s}$, duty cycle $d \leq 2\%$;
2. Drain and source Kelvin contact must be located less than 5 mm from the plastic body.

ADVANCED TECHNICAL INFORMATION

The product presented herein is under development. The Technical Specifications offered are derived from a subjective evaluation of the design, based upon prior knowledge and experience, and constitute a "considered reflection" of the anticipated result. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

ISOPLUS i5-Pak™ (IXTL) Outline



- Leads:
1, 5: Drain
2, 4: Source
3: Gate
6: Isolated

SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.190	.205	4.83	5.21
A1	.102	.118	2.59	3.00
A2	.046	.055	1.17	1.40
b	.045	.055	1.14	1.40
b1	.063	.072	1.60	1.83
b2	.100	.110	2.54	2.79
b3	.058	.068	1.47	1.73
c	.020	.029	0.51	0.74
D	1.020	1.040	25.91	26.42
E	.770	.799	19.56	20.29
e	.150 BSC		3.81 BSC	
L	.780	.820	19.81	20.83
L1	.080	.102	2.03	2.59
Q	.210	.235	5.33	5.97
Q1	.490	.513	12.45	13.03
R	.150	.180	3.81	4.57
R1	.100	.130	2.54	3.30
S	.668	.690	16.97	17.53
T	.801	.821	20.34	20.85
U	.065	.080	1.65	2.03

- Note:
1. TAB 6 - Electrically isolated from the other pins.
2. All leads and tab are tin plated.

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IXYS MOSFETs and IGBTs are covered by	4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2
one or more of the following U.S. patents:	4,850,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2
	4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537